

LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)	ATTY DOCKET NO.	APPLICATION NO
	60889-5001	To be assigned
	APPLICANT	10/800259
	Liu and Gregoire	
FILING DATE	GROUP	
Herewith	To be assigned	

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
R	US 2001/0017390 A1	08/30/01	Long et al. (published application no. 09/808,896)	257	368	
	US 2002/0011635 A1	01/2002	Abe et al.	257	408	
	5,449,937	09/1995	Arimura et al.	257	345	
	5,614,752	03/1997	Takenaka, Kazuhiro	257	408	
	5,920,104	07/1999	Nayak et al.	257	408	
	6,081,010	06/2000	Sanchez, Julian J.	257	345	
	6,147,377	11/14/2000	Liu	257	314	
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	6,258,683	07/10/2001	Besser et al.	438	306	
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	6,285,054	09/04/2001	Liu et al.	257	315	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

R		Lee, W., Hwang, H., "Hot Carrier Degradation for Narrow Width MOSFET with Shallow Trench Isolation," Microelectronics Reliability, Received 07/13/1999, Revised 09/22/1999, 40 (2000), pp. 49-56

EXAMINER	<i>Whele</i>	DATE CONSIDERED	<i>8/4/02</i>
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.